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Index

IEE Proceedings Part I
Solid-State and Electron Devices
Vol. 133, 1986

ABBREVIATIONS

- p paper, address or lecture
- d discussion on a paper
- a abstract of paper or address
- e errata

Author index

A

Abuelma'atti, M.T. Modelling the DC characteristics of VMOS power transistors for computer-aided design p161
Akiba, Y., Supadech, S., Okazaki, S., Kurosu, T., and Iida, M. see Supadech, S.
Allan, D.A. Stability of Schottky barriers at high temperatures for use in GaAs MESFET technology p18
Amaratunga, G.A.J., and Ismail, R. Quasilinear formulation with a simple remeshing scheme for the finite element based simulation of dopant diffusion in silicon p221
Ando, T., Yamasaki, H., and Sugishita, T. Analysis of optical writing mode in solid-state imaging devices with inherent MNOS memory p6

B

Barlow, P.S., Davis, R.G., and Lazarus, M.J. Negative differential output conductance of self heated power MOSFETs p177
Belchamber, R.M., Kingswood, N., Dagless, E.L., Betteridge, D., Lilley, T., and Roberts, J.D.M. see Kingswood, N.
Betteridge, D., Kingswood, N., Dagless, E.L., Belchamber, R.M., Lilley, T., and Roberts, J.D.M. see Kingswood, N.
Bharath Kumar, K., Krishnapur, R., and Mondal, T.B. Accurate bias dependent linear model for bipolar transistors up to 6 GHz p214

C

Carter, R.G., and Srivastava, V. see Srivastava, V.
Chan, A.Y.C., and Juhasz, C. Photo-induced discharge effects of ZnO semiconductor powder-resin binder layers p203
Chang, C.Y., Fang, B.C., Wang, Y.D., and Tzeng, F.C. Isolated Al-SiN-(p)Si-(n)Si MISS device p189
Chang, C.Y., Liu, W.C., Wang, Y.H., and Liao, S.A. see Liu, W.C.
Chester, E.G., Sayers, I.L., and Kinniment, D.J. see Sayers, I.L.
Chinnadurai, R., and Kalyanasundaram, N. see Kalyanasundaram, N.
Choi, Y.I., Kim, C.K., and Kwon, Y.S. Taper etching of the therma. oxide layer p13
Claassen, M., Freyer, J., and Guettich, U. see Freyer, J.

D

Dagless, E.L., Kingswood, N., Belchamber, R.M., Betteridge, D., Lilley, T., and Roberts, J.D.M. see Kingswood, N.
Darby, B.J, and Orton, D.W.R. Structured approaches to design p83
Davis, R.G., Barlow, P.S., and Lazarus, M.J. see Barlow, P.S.
Dorey, A.P. Editorial: Systems on silicon p65

F

Fang, B.C., Chang, C.Y., Wang, Y.D., and Tzeng, F.C. see Chang, C.Y.
Fox, J. Cell-based design: a review p77
Freyer, J., Guettich, U., and Claassen, M. Elimination of surface current induced failure in millimetre-wave Baritt diodes p25

G

Guettich, U., Freyer, J., and Claassen, M. see Freyer, J.

H

Hamer, M.F. First-order parameter extraction on enhancement silicon MOS transistors p49
Henderson, I.A., and McGhee, J. Arbitrary space charge to bulk boundary model of Auger recombination for semiconductor power diodes p169
Hughes, J.R. Contrast variations in high-level multiplexed twisted nematic liquid-crystal displays p145

I

Iida, M., Supadech, S., Okazaki, S., Akiba, Y., and Kurosu, T. see Supadech, S.
Ismail, R., and Amaratunga, G.A.J. see Amaratunga, G.A.J.

J

Jain, S.C., Totterdell, D.H.J., and Leake, J.W. see Totterdell, D.H.J.
Jen, C.-W., Jou, S.-J., Shen, W.-Z., and Lee, C.-L. see Jou, S.-J.
Jeung, Y.C. Novel dynamic random access memory cell using three diodes p61
Jou, S.-J., Jen, C.-W., Shen, W.-Z., and Lee, C.-L. MOTA: a MOSFET timing simulator p193
Juhasz, C., and Chan, A.Y.C. see Chan, A.Y.C.

K

Kalyanasundaram, N., and Chinnadurai, R. Large-signal field analysis of an O-type travelling wave amplifier. Part 2: Numerical results p163
Kemhadjian, H.A. Editorial p201
Kim, C.K., Choi, Y.I., and Kwon, Y.S. see Choi, Y.I.
Kingswood, N., Dagless, E.L., Belchamber, R.M., Betteridge, D., Lilley, T., and Roberts, J.D.M. Image reconstruction using the transputer p99
Kinniment, D.J., Sayers, I.L., and Chester, E.G. see Sayers, I.L.
Kinniment, D.J., and Liesenberg, H.K.E. see Liesenberg, H.K.E.
Krishnapur, R., Bharath Kumar, K., and Mondal, T.B. see Bharath Kumar, K.
Kurosu, T., Supadech, S., Okazaki, S., Akiba, Y., and Iida, M. see Supadech, S.
Kwon, Y.S., Choi, Y.I., and Kim, C.K. see Choi, Y.I.

L

Lazarus, M.J., Barlow, P.S., and Davis, R.G. see Barlow, P.S.
Lea, R.M. SCAPE: a single-chip array processing element for signal and image processing p105
Lea, R.M. VLSI and WSI associative string processors for structured data processing p113
Leake, J.W., Totterdell, D.H.J., and Jain, S.C. see Totterdell, D.H.J.
Lee, C.-L., Jou, S.-J., Jen, C.-W., and Shen, W.-Z. see Jou, S.-J.
Liao, S.A., Liu, W.C., Wang, Y.H., and Chang, C.Y. see Liu, W.C.
Liesenberg, H.K.E., and Kinniment, D.J. Placement expanding autolayout router p55
Lilley, T., Kingswood, N., Dagless, E.L., Belchamber, R.M., Betteridge, D., and Roberts, J.D.M. see Kingswood, N.
Liu, W.C., Wang, Y.H., Chang, C.Y., and Liao, S.A. GaAs $n^+ip^+in^+$ barrier transistor with ultra-thin p^+ AlGaAs base prepared by molecular beam epitaxy p47

M

Manookian, W.Z., and Wilson, J.I.B. Interfacial problems in preparing a-Si : H FETs p153
McGhee, J., and Henderson, I.A. see Henderson, I.A.
Milne, G.J. Behavioural description and VLSI verification p87
Moglestue, C. Hot, tepid and temperate electrons in bulk GaAs p35
Mondal, T.B., Bharath Kumar, K., and Krishnapur, R. see Bharath Kumar, K.

O

Okazaki, S., Supadech, S., Akiba, Y., Kurosu, T., and Iida, M. see Supadech, S.
Oldfield, J.V. Logic programs and an experimental architecture for their execution p123
Orton, D.W.R., and Darby, B.J see Darby, B.J

P

Partridge, S.L. Silicon-on-insulator technology p66

R

Renshaw, D. Workshop on integrated CAD and workstations, 1985 Systems on silicon seminar p141
Roberts, J.D.M., Kingswood, N., Dagless, E.L., Belchamber, R.M., Betteridge, D., and Lilley, T. see Kingswood, N.

S

Sayers, I.L., Kinniment, D.J., and Chester, E.G. Design of a reliable and self-testing VLSI datapath using residue coding techniques p129
Shen, W.-Z., Jou, S.-J., Jen, C.-W., and Lee, C.-L. see Jou, S.-J.
Srivastava, V., and Carter, R.G. Effect of boundaries on the space charge potential in coupled cavity travelling wave tubes p185
Sugishita, T., Ando, T., and Yamasaki, H. see Ando, T.
Supadech, S., Okazaki, S., Akiba, Y., Kurosu, T., and Iida, M. Voltage-controlled negative resistance in p^+-i-n^+ planar diodes with injection gate p1

T

Totterdell, D.H.J., Leake, J.W., and Jain, S.C. High-injection open-circuit voltage decay in pn-junction diodes with lightly doped bases p181
Tzeng, F.C., Chang, C.Y., Fang, B.C., and Wang, Y.D. see Chang, C.Y.

W

Wang, Y.D., Chang, C.Y., Fang, B.C., and Tzeng, F.C. see Chang, C.Y.
Wang, Y.H., Liu, W.C., Chang, C.Y., and Liao, S.A. see Liu, W.C.
Wilson, J.I.B., and Manookian, W.Z. see Manookian, W.Z.

Y

Yamasaki, H., Ando, T., and Sugishita, T. see Ando, T.

AMPLIFIERS

Large-signal field analysis of an O-type travelling wave amplifier. Part 2: Numerical results. N. Kalyanasundaram and R. Chinnadurai p163

BIPOLAR TRANSISTORS

Accurate bias dependent linear model for bipolar transistors up to 6 GHz. K. Bharath Kumar, R. Krishnapur and T.B. Mondal p214

CIRCUIT THEORY AND DESIGN

Behavioural description and VLSI verification. G.J. Milne p87
Cell-based design: a review. J. Fox p77
Design of a reliable and self-testing VLSI datapath using residue coding techniques. I.L. Sayers, D.J. Kinniment and E.G. Chester p129
Placement expanding autolayout router. H.K.E. Liesenberg and D.J. Kinniment p55
Structured approaches to design. B.J Darby and D.W.R. Orton p83

CODES AND DECODING

Design of a reliable and self-testing VLSI datapath using residue coding techniques. I.L. Sayers, D.J. Kinniment and E.G. Chester p129

COMPUTER APPLICATIONS

Editorial: Systems on silicon. A.P. Dorey p65
Image reconstruction using the transputer. N. Kingswood, E.L. Dagless, R.M. Belchamber, D. Betteridge, T. Lilley and J.D.M. Roberts p99
Logic programs and an experimental architecture for their execution. J.V. Oldfield p123

COMPUTER-AIDED DESIGN

Modelling the DC characteristics of VMOS power transistors for computer-aided design. M.T. Abuelma'atti p161
Workshop on integrated CAD and workstations, 1985 Systems on silicon seminar. D. Renshaw p141

DIGITAL CIRCUITS

Design of a reliable and self-testing VLSI datapath using residue coding techniques. I.L. Sayers, D.J. Kinniment and E.G. Chester p129

DIODES

Arbitrary space charge to bulk boundary model of Auger recombination for semiconductor power diodes. I.A. Henderson and J. McGhee p169
Elimination of surface current induced failure in millimetre-wave Baritt diodes. J. Freyer, U. Guettich and M. Claassen p25
High-injection open-circuit voltage decay in *pn*-junction diodes with lightly doped bases. D.H.J. Totterdell, J.W. Leake and S.C. Jain p181
Novel dynamic random access memory cell using three diodes. Y.C. Jeung p61
Voltage-controlled negative resistance in p^+-i-n^+ planar diodes with injection gate. S. Supadech, S. Okazaki, Y. Akiba, T. Kurosu and M. Iida p1

DISCHARGES, ELECTRIC

Photo-induced discharge effects of ZnO semiconductor powder-resin binder layers. A.Y.C. Chan and C. Juhasz p203

DOPING

Quasilinear formulation with a simple remeshing scheme for the finite element based simulation of dopant diffusion in silicon. G.A.J. Amaratunga and R. Ismail p221

ELECTROMAGNETIC THEORY

Effect of boundaries on the space charge potential in coupled cavity travelling wave tubes. V. Srivastava and R.G. Carter p185

ELECTRON DEVICES

Effect of boundaries on the space charge potential in coupled cavity travelling wave tubes. V. Srivastava and R.G. Carter p185
Hot, tepid and temperate electrons in bulk GaAs. C. Moglestue p35
Large-signal field analysis of an O-type travelling wave amplifier. Part 2: Numerical results. N. Kalyanasundaram and R. Chinnadurai p163

EPITAXY

GaAs $n^+i\delta p^+in^+$ barrier transistor with ultra-thin p^+AlGaAs base prepared by molecular beam epitaxy. W.C. Liu, Y.H. Wang, C.Y. Chang and S.A. Liao p47

FEEDBACK

Placement expanding autolayout router. H.K.E. Liesenberg and D.J. Kinniment p55

FIELD-EFFECT TRANSISTORS

Interfacial problems in preparing a-Si : H FETs. W.Z. Manookian and J.I.B. Wilson p153
MOTA: a MOSFET timing simulator. S.-J. Jou, C.-W. Jen, W.-Z. Shen and C.-L. Lee p193
Negative differential output conductance of self heated power MOSFETs. P.S. Barlow, R.G. Davis and M.J. Lazarus p177
Stability of Schottky barriers at high temperatures for use in GaAs MESFET technology. D.A. Allan p18

IMAGE PROCESSING

SCAPE: a single-chip array processing element for signal and image processing. R.M. Lea p105

INFORMATION AND COMMUNICATION THEORY

VLSI and WSI associative string processors for structured data processing. R.M. Lea p113

INTEGRATED CIRCUITS

Placement expanding autolayout router. H.K.E. Liesenberg and D.J. Kinniment p55
Taper etching of the thermal oxide layer. Y.I. Choi, C.K. Kim and Y.S. Kwon p13

LOGIC

Logic programs and an experimental architecture for their execution. J.V. Oldfield p123

METAL-INSULATOR-SEMICONDUCTOR STRUCTURES

Isolated Al-SiN-(p)Si-(n)Si MISS device. C.Y. Chang, B.C. Fang, Y.D. Wang and F.C. Tzeng p189

METAL-OXIDE-SEMICONDUCTOR STRUCTURES

First-order parameter extraction on enhancement silicon MOS transistors. M.F. Hamer p49
MOTA: a MOSFET timing simulator. S.-J. Jou, C.-W. Jen, W.-Z. Shen and C.-L. Lee p193
Negative differential output conductance of self heated power MOSFETs. P.S. Barlow, R.G. Davis and M.J. Lazarus p177
Silicon-on-insulator technology. S.L. Partridge p66

MODELLING

Accurate bias dependent linear model for bipolar transistors up to 6 GHz. K. Bharath Kumar, R. Krishnapur and T.B. Mondal p214
Analysis of optical writing mode in solid-state imaging devices with inherent MNOS memory. T. Ando, H. Yamasaki and T. Sugishita p6
Hot, tepid and temperate electrons in bulk GaAs. C. Moglestue p35
Modelling the DC characteristics of VMOS power transistors for computer-aided design. M.T. Abuelma'atti p161
Voltage-controlled negative resistance in p^+-i-n^+ planar diodes with injection gate. S. Supadech, S. Okazaki, Y. Akiba, T. Kurosu and M. Iida p1

OPTICAL SENSORS

Photo-induced discharge effects of ZnO semiconductor powder-resin binder layers. A.Y.C. Chan and C. Juhasz p203

OPTOELECTRONICS

Analysis of optical writing mode in solid-state imaging devices with inherent MNOS memory. T. Ando, H. Yamasaki and T. Sugishita p6
Contrast variations in high-level multiplexed twisted nematic liquid-crystal displays. J.R. Hughes p145
Photo-induced discharge effects of ZnO semiconductor powder-resin binder layers. A.Y.C. Chan and C. Juhasz p203

PERMITTIVITY

Contrast variations in high-level multiplexed twisted nematic liquid-crystal displays. J.R. Hughes p145

POWER ELECTRONICS

Arbitrary space charge to bulk boundary model of Auger recombination for semiconductor power diodes. I.A. Henderson and J. McGhee p169
Modelling the DC characteristics of VMOS power transistors for computer-aided design. M.T. Abuelma'atti p161

RADIATION

Image reconstruction using the transputer. N. Kingswood, E.L. Dagless, R.M. Belchamber, D. Betteridge, T. Lilley and J.D.M. Roberts p99

SCHOTTKY-BARRIER DEVICES

Novel dynamic random access memory cell using three diodes. Y.C. Jeung p61
Stability of Schottky barriers at high temperatures for use in GaAs MESFET technology. D.A. Allan p18

SEMICONDUCTOR DEVICES AND MATERIALS

Analysis of optical writing mode in solid-state imaging devices with inherent MNOS memory. T. Ando, H. Yamasaki and T. Sugishita p6
Arbitrary space charge to bulk boundary model of Auger recombination for semiconductor power diodes. I.A. Henderson and J. McGhee p169
Cell-based design: a review. J. Fox p77
Elimination of surface current induced failure in millimetre-wave Baritt diodes. J. Freyer, U. Guettich and M. Claassen p25
First-order parameter extraction on enhancement silicon MOS transistors. M.F. Hamer p49
GaAs $n^+i\delta p^+in^+$ barrier transistor with ultra-thin p^+AlGaAs base prepared by molecular beam epitaxy. W.C. Liu, Y.H. Wang, C.Y. Chang and S.A. Liao p47
High-injection open-circuit voltage decay in *pn*-junction diodes with lightly doped bases. D.H.J. Totterdell, J.W. Leake and S.C. Jain p181
Hot, tepid and temperate electrons in bulk GaAs. C. Moglestue p35
Interfacial problems in preparing a-Si : H FETs. W.Z. Manookian and J.I.B. Wilson p153
Isolated Al-SiN-(p)Si-(n)Si MISS device. C.Y. Chang, B.C. Fang, Y.D. Wang and F.C. Tzeng p189
Novel dynamic random access memory cell using three diodes. Y.C. Jeung p61
Photo-induced discharge effects of ZnO semiconductor powder-resin binder layers. A.Y.C. Chan and C. Juhasz p203

Quasilinear formulation with a simple remeshing scheme for the finite element based simulation of dopant diffusion in silicon. G.A.J. Amaratunga and R. Ismail p221
Silicon-on-insulator technology. S.L. Partridge p66
Stability of Schottky barriers at high temperatures for use in GaAs MESFET technology. D.A. Allan p18
Taper etching of the thermal oxide layer. Y.I. Choi, C.K. Kim and Y.S. Kwon p13
Voltage-controlled negative resistance in p^+-i-n^+ planar diodes with injection gate. S. Supadech, S. Okazaki, Y. Akiba, T. Kurosu and M. Iida p1

SIGNAL PROCESSING

SCAPE: a single-chip array processing element for signal and image processing. R.M. Lea p105
VLSI and WSI associative string processors for structured data processing. R.M. Lea p113

SIMULATION

Hot, tepid and temperate electrons in bulk GaAs. C. Moglestue p35
MOTA: a MOSFET timing simulator. S.-J. Jou, C.-W. Jen, W.-Z. Shen and C.-L. Lee p193
Quasilinear formulation with a simple remeshing scheme for the finite element based simulation of dopant diffusion in silicon. G.A.J. Amaratunga and R. Ismail p221

STABILITY

Stability of Schottky barriers at high temperatures for use in GaAs MESFET technology. D.A. Allan p18

TRANSISTORS

Accurate bias dependent linear model for bipolar transistors up to 6 GHz. K. Bharath Kumar, R. Krishnapur and T.B. Mondal p214
First-order parameter extraction on enhancement silicon MOS transistors. M.F. Hamer p49
GaAs $n^+ip^+in^+$ barrier transistor with ultra-thin p^+AlGaAs base prepared by molecular beam epitaxy. W.C. Liu, Y.H. Wang, C.Y. Chang and S.A. Liao p47
Interfacial problems in preparing a-Si : H FETs. W.Z. Manookian and J.I.B. Wilson p153
Modelling the DC characteristics of VMOS power transistors for computer-aided design. M.T. Abuelma'atti p161

VERY LARGE SCALE INTEGRATION

Behavioural description and VLSI verification. G.J. Milne p87
Cell-based design: a review. J. Fox p77
Design of a reliable and self-testing VLSI datapath using residue coding techniques. I.L. Sayers, D.J. Kinniment and E.G. Chester p129
Editorial: Systems on silicon. A.P. Dorey p65
Novel dynamic random access memory cell using three diodes. Y.C. Jeung p61
SCAPE: a single-chip array processing element for signal and image processing. R.M. Lea p105
Silicon-on-insulator technology. S.L. Partridge p66
Structured approaches to design. B.J Darby and D.W.R. Orton p83
VLSI and WSI associative string processors for structured data processing. R.M. Lea p113

WAVEGUIDES AND WAVEGUIDE COMPONENTS

Effect of boundaries on the space charge potential in coupled cavity travelling wave tubes. V. Srivastava and R.G. Carter p185